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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/857,859 09/17/2001		Bernd Heinemann	7040-30	2690	
21324	7590 07/18/2003				
HAHN LOESER & PARKS, LLP TWIN OAKS ESTATE 1225 W. MARKET STREET AKRON, OH 44313			EXAMINER		
			NGUYEN, TUAN H		
			ART UNIT	PAPER NUMBER	
				TALEK HÖMBEK	
			2813		
			DATE MAILED: 07/18/2003		

Please find below and/or attached an Office communication concerning this application or proceeding.

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<u>`</u>	,		Application No.	Applicant(s)
ř			09/857,859	HEINEMANN ET AL.
	Offic	Action Summary	Examiner	Art Unit
			Tuan H. Nguyen	2813
Peri d	The MAIL for Reply	LING DATE of this commun	ication appears on the c ver sheet w	ith the c rrespondence address
THE - Ex aft - If t - If t - Fa - An	E MAILING E tensions of time r ter SIX (6) MONTI the period for reply NO period for repl tilure to reply withing ty reply received by	DATE OF THIS COMMUNI may be available under the provisions HS from the mailing date of this comm y specified above is less than thirty (3 y is specified above, the maximum sta in the set or extended period for reply	of 37 CFR 1.136(a). In no event, however, may a	reply be timely filed  ty (30) days will be considered timely.  ITHS from the mailing date of this communication.  BANDONED (35 U.S.C. § 133).
Status	_			
1)⊠	_	• •	ed on <u>17 September 2001</u> .	
2a)[_	=		2b)⊠ This action is non-final.	
3)[			n for allowance except for formal ma tice under <i>Ex parte Quayle</i> , 1935 C.	tters, prosecution as to the merits is
Disp s	ition of Clai		ilice under Ex parte Quayre, 1955 C.	D. 11, 400 O.G. 210.
4)⊠	Claim(s)	1-14 is/are pending in the	application.	
	4a) Of the	above claim(s) is/a	re withdrawn from consideration.	
5)[	Claim(s)	is/are allowed.		·
6)⊠	Claim(s) 1	<u>1-14</u> is/are rejected.		
7)□		is/are objected to.		
8)□	Claim(s)	are subject to restric	etion and/or election requirement.	
Applica	ation Papers	<b>5</b>		
9)[	The specifi	ication is objected to by the	e Examiner.	
10)[	The drawin	ng(s) filed on is/are:	a) ☐ accepted or b) ☐ objected to by t	he Examiner.
	Applicant	may not request that any obj	ection to the drawing(s) be held in abey	ance. See 37 CFR 1.85(a).
11)[	The propos	sed drawing correction filed	d on is: a)☐ approved b)☐ d	disapproved by the Examiner.
	If approve	ed, corrected drawings are re	quired in reply to this Office action.	
12)[	The oath o	r declaration is objected to	by the Examiner.	
Pri rity	under 35 U	J.S.C. §§ 119 and 120		
13)⊠	Acknowle	dgment is made of a claim	for foreign priority under 35 U.S.C.	§ 119(a)-(d) or (f).
a	a)⊠ All b)□	☐ Some * c)☐ None of:		
	1.⊠ Cer	tified copies of the priority	documents have been received.	
	2. Cer	tified copies of the priority	documents have been received in A	application No
si si		application from the Intern	of the priority documents have been ational Bureau (PCT Rule 17.2(a)). n for a list of the certified copies not	
14)[	Acknowledg	gment is made of a claim f	or domestic priority under 35 U.S.C.	§ 119(e) (to a provisional application).
15)			nguage provisional application has b for domestic priority under 35 U.S.C.	
Attachm	ent(s)			
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2) Notice of Draftsperson's Patent Drawing Review (PTO-948)

3) Information Disclosure Statement(s) (PTO-1449) Paper No(s) 3.

4) Interview	Summary (PTO-413) Paper No(s).
5) Notice of	Informal Patent Application (PTO-152)
6) Dother:	

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#### **DETAILED ACTION**

### Claim Rejections - 35 USC § 112

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claims 1-14 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Claim 1 is indefinite since it does not positively recite the process steps.

In claims 1, lines 4-5; claim 8, line 3; claim 14, line 6, "buffer layer can be deposited" is indefinite since it is unclear as whether the buffer layer is deposited or not;.

In claim 1, line 6; claim 8, line 5, "the effective emitter zone" lacks antecedent basis.

#### Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The changes made to 35 U.S.C. 102(e) by the American Inventors Protection Act of 1999 (AIPA) and the Intellectual Property and High Technology Technical

Amendments Act of 2002 do not apply when the reference is a U.S. patent resulting

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directly or indirectly from an international application filed before November 29, 2000. Therefore, the prior art date of the reference is determined under 35 U.S.C. 102(e) prior to the amendment by the AIPA (pre-AIPA 35 U.S.C. 102(e)).

Claims 1, 8, 12-14 are rejected under 35 U.S.C. 102(e) as being anticipated by Koscielniak et al..

See Koscielnak et al., figs. 1-16 and related text on col. 4-10 which discloses the claimed method for forming a bipolar transistor structure including the steps of producing on a monocrystal substrate 200 a collector region 201, 202 and insulation region 204 surrounding the collector region (fig. 1, col. 4, last two paragraphs); producing a base layer 205-1 and a cap layer 205-2 over the collector region by epitaxy (fig. 2, col. 5, second to fourth paragraphs); depositing an insulation layer 207-1, 207-2 over the cap layer 205-2, the insulation layer opened in an area of an effective emitter zone (fig. 12, col. 9, second paragraph); and depositing and structuring a polysilicon layer 292 over the opened insulating layer 207 and using this layer as a source of emitter doping agent and as a contact layer (figs. 15-16, col. 9, last two paragraphs); wherein a doping profile is introduced into the cap layer 205-2, the profiled being low doped on a base side thereof and high doped on an emitter side thereof (col. 5, lines 44-48).

With respect to claim 13, bottom part of the base layer 205-1 is considered as a buffer layer.

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## Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 2-7, 9-11 are rejected under 35 U.S.C. 103(a) as being unpatentable over Koscielniak et al.

Koscielniak et al., figs. 1-16, and text on col. 4-10 discloses substantially the claimed method for producing a bipolar transistor as explained above, including a doping profile is introduced into the cap layer 205-2, the profile ranges from approximately 2x10<sup>18</sup>/cm<sup>2</sup> at an upper surface of layer 205-2 to approximately 1x10<sup>17</sup>cm<sup>2</sup> at a lower surface of the layer 205-2 and the layer 205-2 has a thickness ranging from about 700-1400 angstroms (col. 5, lines 44-50).

Koscielniak et al. lacks anticipation of using different techniques for doping the cap layer as claimed in claims 5-7, or the base side lower doping concentration of the cap layer as claimed in claims 2, 9, or the dopant type for the emitter-side cap layer as claimed in claims 4, 11.

It would have been obvious to one having ordinary skill in the art at the timethe invention was made to have used either implantation, diffusion of in-situ doping processes for introducing dopant in the cap layer since they are well-known techniques in the semiconductor processing art, and selected a suitable dopant type, concentration for obtaining an optimum result.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Tuan H. Nguyen whose telephone number is 703-308-2550. The examiner can normally be reached on 9AM-5:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead Jr. can be reached on 703-308-4940. The fax phone numbers for the organization where this application or proceeding is assigned are 703-305-3431 for regular communications and 703-305-3432 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

Tuan H. Ngúyen Primary Examiner Art Unit 2813

TN July 14, 2003